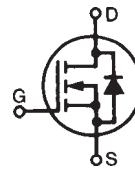


**Polar™ Power MOSFET**  
**HiPerFET™**

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

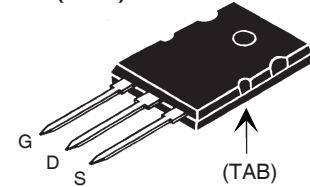
**IXFK20N120P**  
**IXFX20N120P**



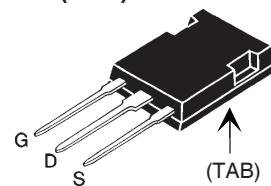
**V<sub>DSS</sub>** = 1200V  
**I<sub>D25</sub>** = 20A  
**R<sub>DS(on)</sub>** ≤ 570mΩ  
**t<sub>rr</sub>** ≤ 300ns

Symbol	Test Conditions	Maximum Ratings		
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1200		V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	1200		V
V <sub>GSS</sub>	Continuous	± 30		V
V <sub>GSM</sub>	Transient	± 40		V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	20		A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	50		A
I <sub>A</sub>	T <sub>C</sub> = 25°C	10		A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	1		J
dV/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	15		V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	780		W
T <sub>J</sub>		-55 ... +150		°C
T <sub>JM</sub>		150		°C
T <sub>stg</sub>		-55 ... +150		°C
T <sub>L</sub>	1.6mm (0.062 in.) from case for 10s	300		°C
T <sub>SOLD</sub>	Plastic body for 10s	260		°C
M <sub>d</sub>	Mounting torque (IXFK)	1.13/10		Nm/lb.in.
F <sub>c</sub>	Mounting force (IXFX)	20..120 / 4.5..27		N/lb.
Weight	TO-264 PLUS247	10 6		g g

**TO-264 (IXFK)**



**PLUS247 (IXFX)**



G = Gate      D = Drain  
S = Source      TAB = Drain

Symbol	Test Conditions (T <sub>J</sub> = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	1200		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA	3.5		V
I <sub>GSS</sub>	V <sub>GS</sub> = ± 30V, V <sub>DS</sub> = 0V		± 200	nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0V		25	μA
		T <sub>J</sub> = 125°C	5	mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1		570	mΩ

**Features**

- Fast intrinsic diode
- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

**Advantages**

- Easy to mount
- Space savings
- High power density

**Applications:**

- High Voltage Switched-mode and resonant-mode power supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC converters
- High Voltage DC-AC inverters

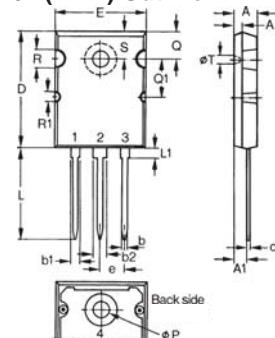
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	10	16	S
$C_{iss}$ $C_{oss}$ $C_{rss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	11.1	nF	
		600	pF	
		60	pF	
$R_{Gi}$	Gate input resistance	1.60		$\Omega$
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)	49		ns
		45		ns
		72		ns
		70		ns
$Q_{g(on)}$ $Q_{gs}$ $Q_{gd}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$	193		nc
		74		nc
		85		nc
$R_{thJC}$			0.16	$^\circ\text{C}/\text{W}$
$R_{thCS}$		0.15		$^\circ\text{C}/\text{W}$

**Source-Drain Diode**

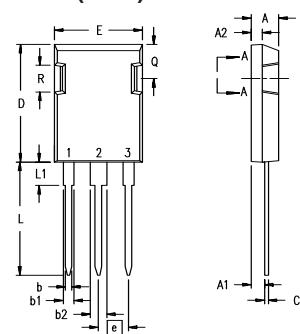
**Characteristic Values**  
 $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{V}$		20	A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$		80	A
$V_{SD}$	$I_F = I_s$ , $V_{GS} = 0\text{V}$ , Note 1		1.5	V
$t_{rr}$ $Q_{RM}$ $I_{RM}$	$I_F = 10\text{A}$ , $-\frac{dI}{dt} = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$	0.84	300	ns
		9	$\mu\text{C}$	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

**TO-264 (IXFK) Outline**


Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

**PLUS247™ (IXFX) Outline**


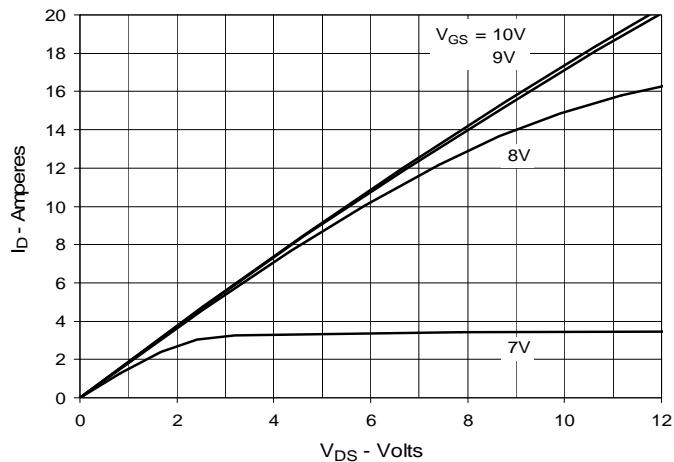
Terminals:  
 1 - Gate  
 2 - Drain (Collector)  
 3 - Source (Emitter)  
 4 - Drain (Collector)

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45	BSC	.215	BSC
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

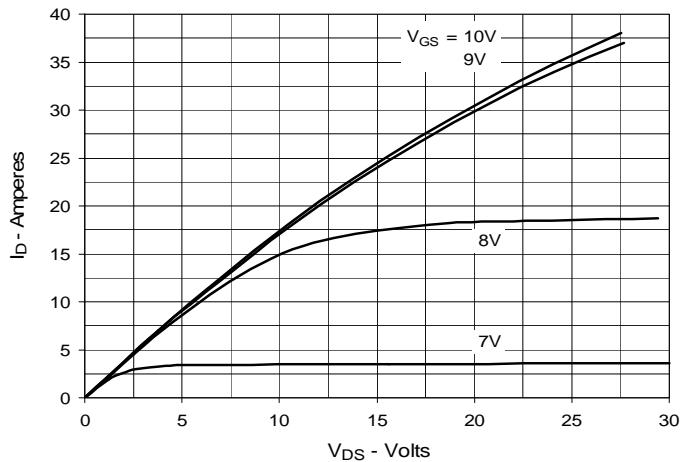
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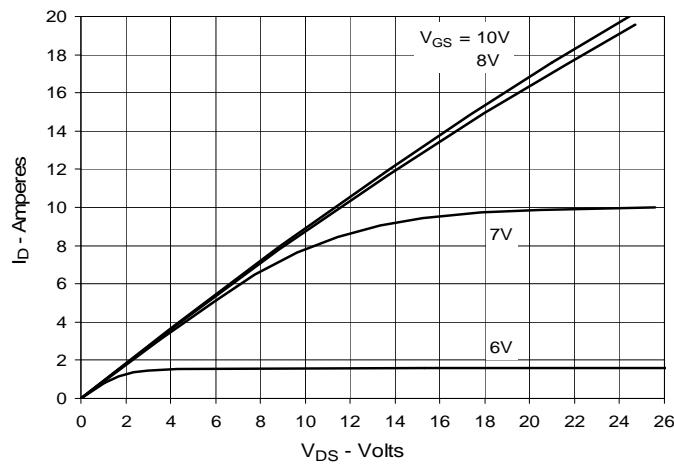
**Fig. 1. Output Characteristics  
@ 25°C**



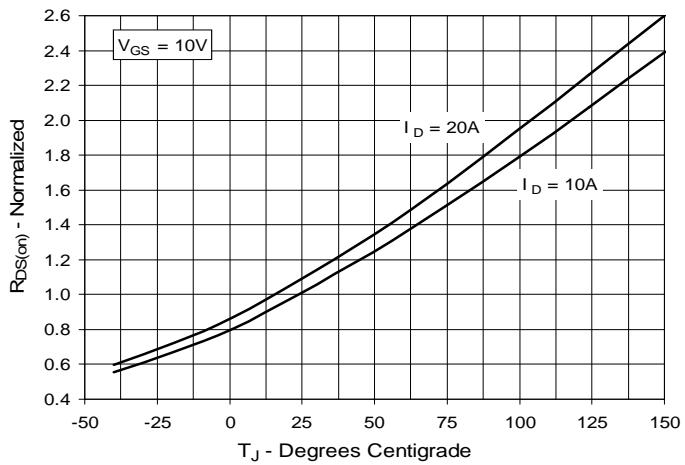
**Fig. 2. Extended Output Characteristics  
@ 25°C**



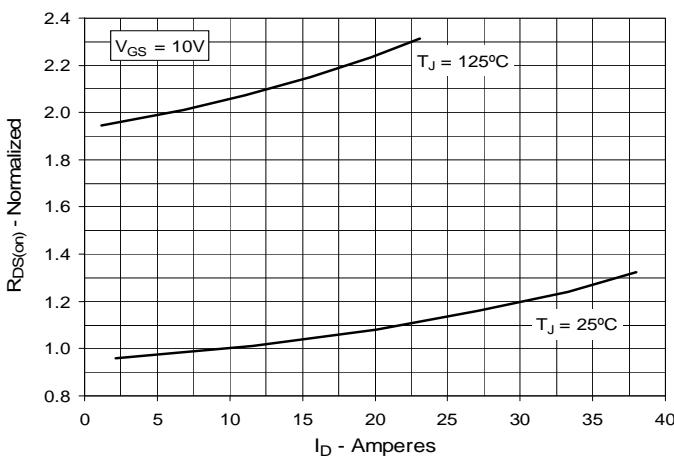
**Fig. 3. Output Characteristics  
@ 125°C**



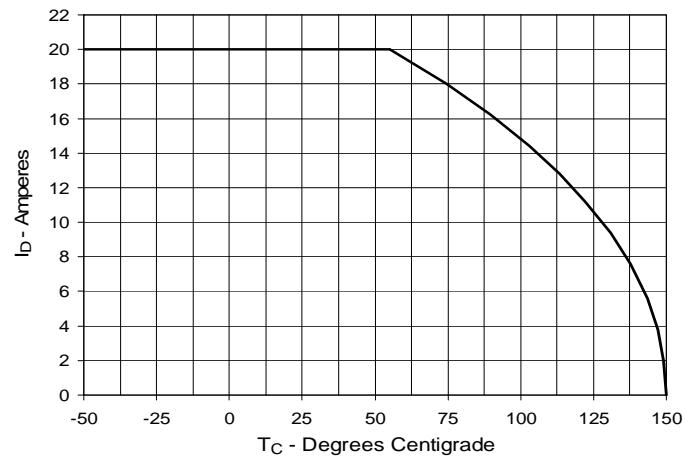
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 10A$  Value  
vs. Junction Temperature**

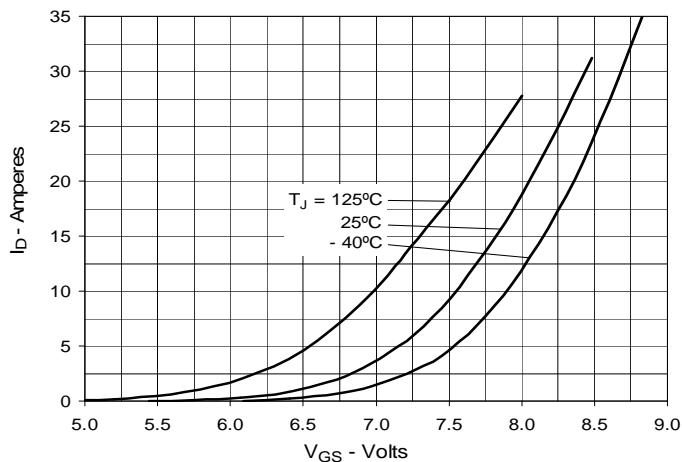
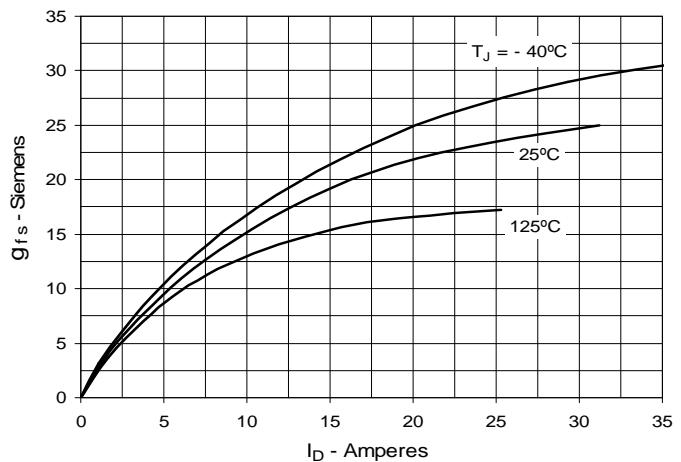
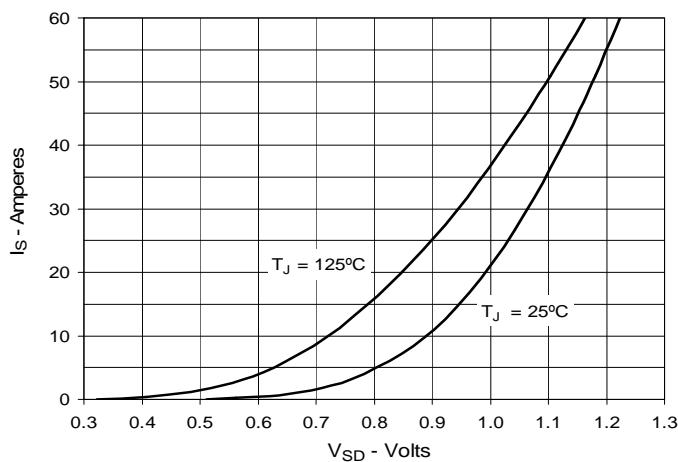
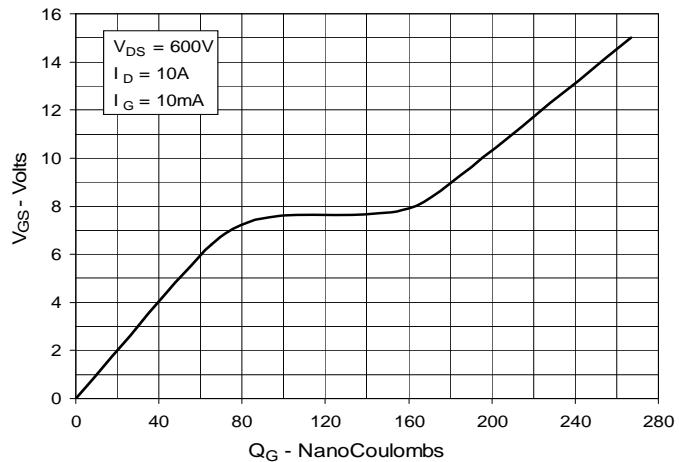
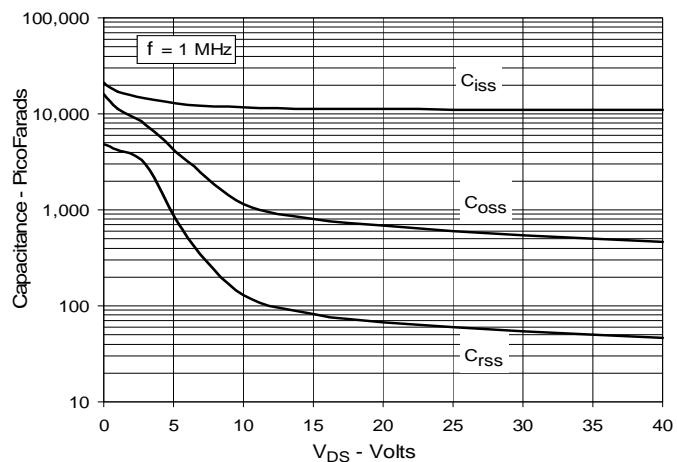
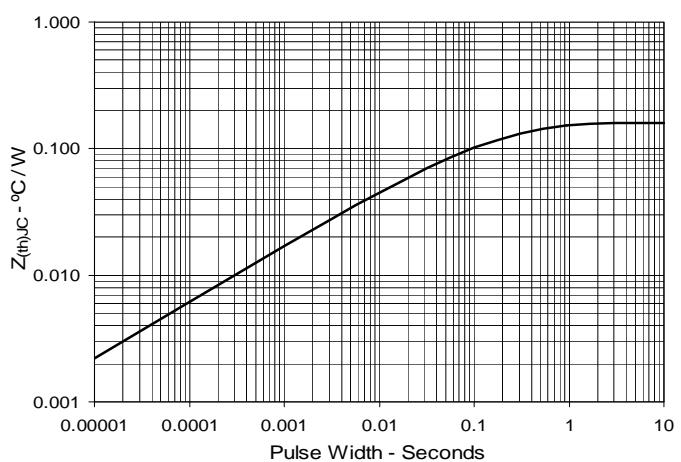


**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 10A$  Value  
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.  
Case Temperature**



**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Maximum Transient Thermal Impedance**


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